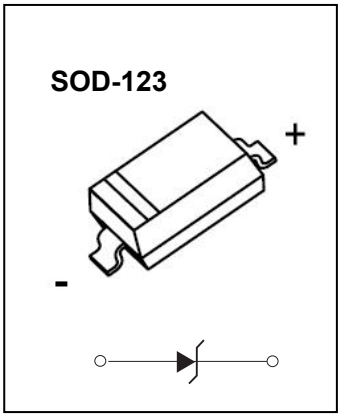
SOD-123 Plastic-Encapsulate Diodes

FEATURES：

- Planar Die Construction
- 350mW Power Dissipation on Ceramic PCB
- General Purpose, Medium Current
- Ideally Suited for Automated Assembly Processes
- Available in Lead Free Version



Maximum Ratings(T_a=25℃ unless otherwise specified)

Characteristic	Symbol	Value	Unit
Forward Voltage (Note 2) @ I_F = 10mA	V_F	0.9	V
Power Dissipation(Note 1)	P_D	350	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

Type Number	Type Code	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current (Note 2)		Typical Temperature Coefficent @I_{ZTC}		Test Current I_{ZTC}
		V_Z@I_{ZT}			I_{ZT}	Z_{ZT}@I_{ZT}	Z_{ZK}@I_{ZK}	I_{ZK}	I_R	V_R	mV/°C		
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V	Min	Max	mA
TKBZT52C2V4	WX	2.4	2.20	2.60	5	100	600	1.0	50	1.0	-3.5	0	5
TKBZT52C2V7	W1	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0	5
TKBZT52C3V0	W2	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0	5
TKBZT52C3V3	W3	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0	5
TKBZT52C3V6	W4	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0	5
TKBZT52C3V9	W5	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0	5
TKBZT52C4V3	W6	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0	5
TKBZT52C4V7	W7	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2	5
TKBZT52C5V1	W8	5.1	4.8	5.4	5	60	480	1.0	2	2.0	-2.7	1.2	5
TKBZT52C5V6	W9	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5	5
TKBZT52C6V2	WA	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7	5
TKBZT52C6V8	WB	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5	5
TKBZT52C7V5	WC	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3	5
TKBZT52C8V2	WD	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2	5
TKBZT52C9V1	WE	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0	5
TKBZT52C10	WF	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0	5
TKBZT52C11	WG	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0	5
TKBZT52C12	WH	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0	5
TKBZT52C13	WI	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0	5
TKBZT52C15	WJ	15	13.8	15.6	5	30	200	1.0	0.1	10.5	9.2	13.0	5
TKBZT52C16	WK	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0	5
TKBZT52C18	WL	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0	5
TKBZT52C20	WM	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0	5
TKBZT52C22	WN	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0	5
TKBZT52C24	WO	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0	5
TKBZT52C27	WP	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3	2
TKBZT52C30	WQ	30	28.0	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4	2
TKBZT52C33	WR	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4	2
TKBZT52C36	WS	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4	2
TKBZT52C39	WT	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2	2
TKBZT52C43	WU	43	40.0	46.0	5	100	700	1.0	0.1	32	10.0	12.0	5

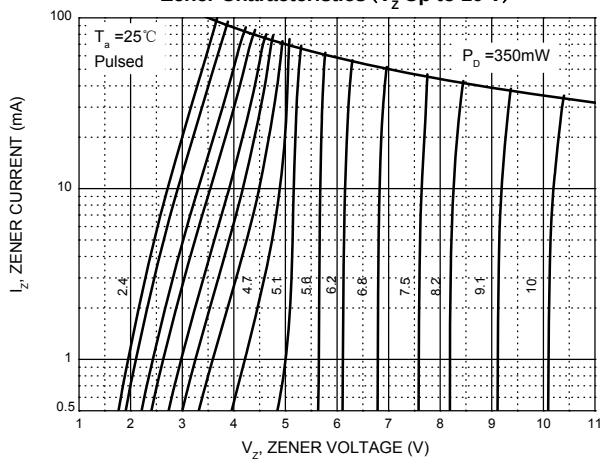
Notes: 1. Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm^2

2. Short duration test pulse used to minimize self-heating effect

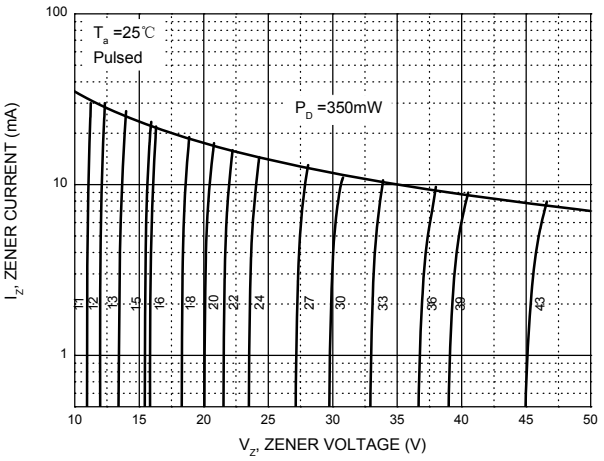
3. f=1kHz

Typical Characteristics

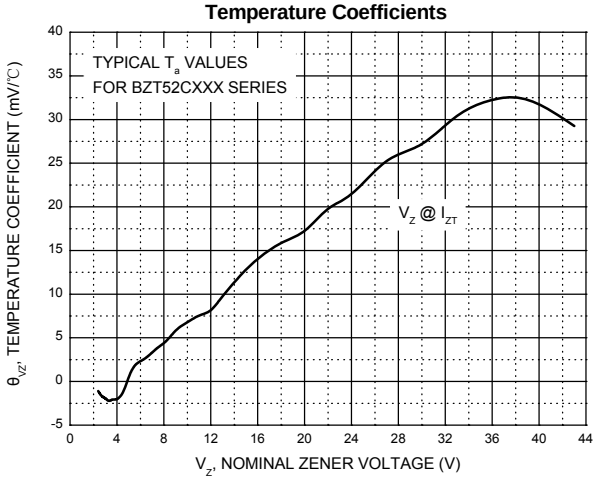
Zener Characteristics (V_Z Up to 10 V)



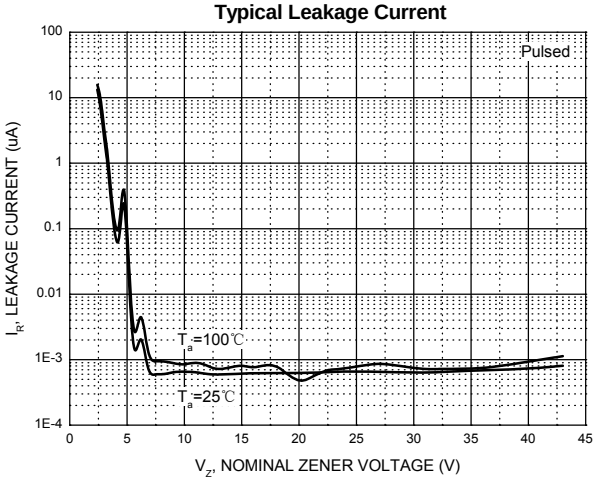
Zener Characteristics (11 V to 43 V)



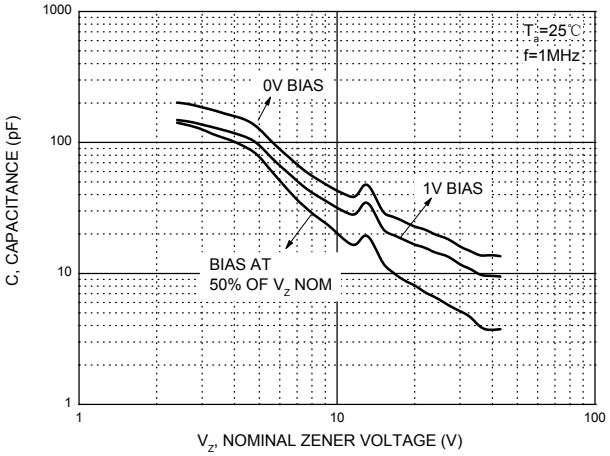
Temperature Coefficients



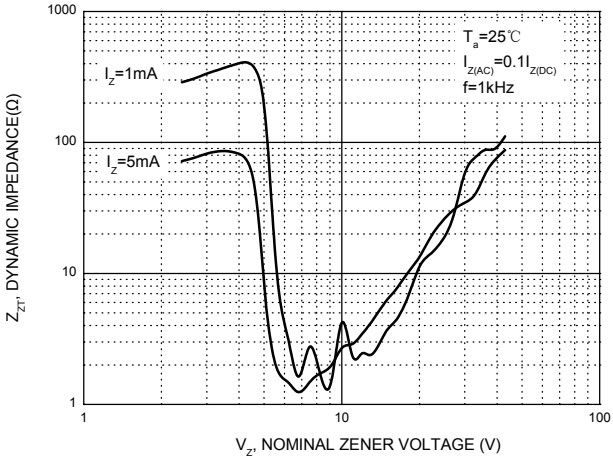
Typical Leakage Current



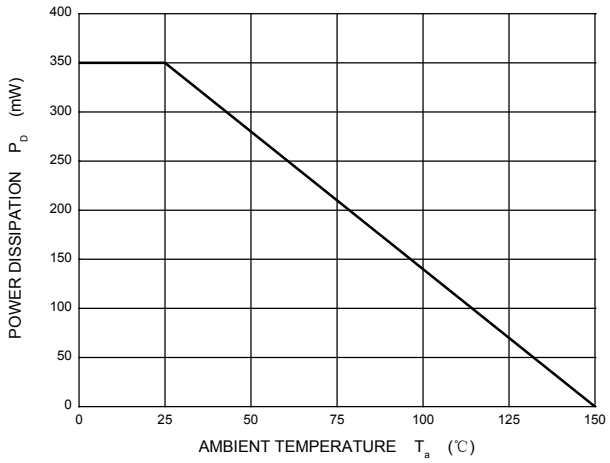
Typical Capacitance

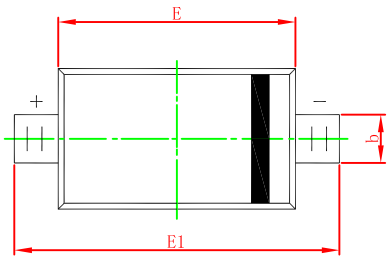


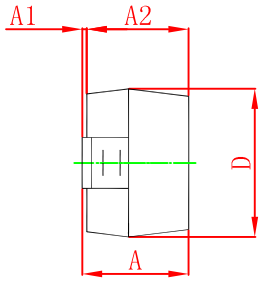
Effect of Zener Voltage on Zener Impedance

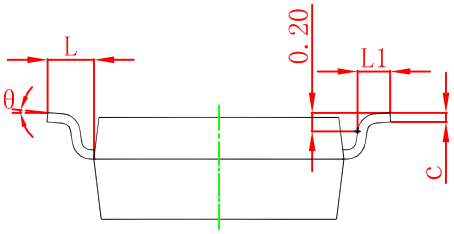


Power Derating Curve



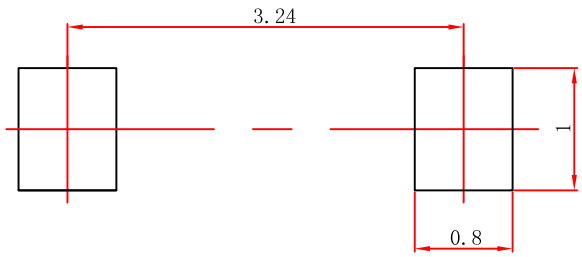






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

SOD-123 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.